

| T | h۵ | rm | ıal | P | es | iet | an | 6 |
|---|----|------|-----|------------------|------------|-----|------|----|
| | пе | :111 | ıaı | \boldsymbol{r} | E 5 | เอเ | .aii | CE |

| Junction - soldering point ¹⁾ | R _{thJS} | ≤ 140 | K/W |
|--|-------------------|-------|-----|
|--|-------------------|-------|-----|

Electrical Characteristics at T_A =25°C, unless otherwise specified

| Parameter | Symbol | Values | | | Unit | |
|--|----------------------|--------|------|------|------|--|
| | | min. | typ. | max. | 1 | |
| DC Characteristics for NPN Type | | | | | • | |
| Collector-emitter breakdown voltage | V _{(BR)CEO} | 50 | - | - | V | |
| $I_{\rm C} = 100 \ \mu \text{A}, \ I_{\rm B} = 0$ | | | | | | |
| Collector-base breakdown voltage | V _{(BR)CBO} | 50 | - | - | | |
| $I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$ | | | | | | |
| Collector cutoff current | I _{CBO} | - | - | 100 | nA | |
| $V_{\rm CB} = 40 \text{ V}, I_{\rm E} = 0$ | | | | | | |
| Emitter cutoff current | I _{EBO} | - | - | 164 | μA | |
| $V_{\rm EB} = 10 \rm V, I_{\rm C} = 0$ | | | | | | |
| DC current gain 2) | h _{FE} | 70 | - | - | - | |
| $I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 5 V | | | | | | |
| Collector-emitter saturation voltage2) | V _{CEsat} | - | - | 0.3 | V | |
| $I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 0.5 mA | | | | | | |
| Input off voltage | $V_{i(off)}$ | 8.0 | - | 1.5 | | |
| $I_{\rm C}$ = 100 μ A, $V_{\rm CE}$ = 5 V | | | | | | |
| Input on Voltage | V _{i(on)} | 1 | - | 3 | | |
| $I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 0.3 V | , , | | | | | |
| Input resistor | R ₁ | 32 | 47 | 62 | kΩ | |
| Resistor ratio | R_1/R_2 | 0.9 | 1 | 1.1 | - | |
| AC Characteristics for NPN Type | | | | | | |
| Transition frequency | f _T | - | 100 | - | MHz | |
| $I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 5 V, f = 100 MHz | | | | | | |
| Collector-base capacitance | C _{cb} | - | 3 | - | pF | |
| $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$ | | | | | | |

 $^{^{1}}$ For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

²⁾ Pulse test: $t < 300 \mu s$; D < 2%



Electrical Characteristics at T_A =25°C, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|--|--------------------|--------|-------|-------|------|
| | | min. | typ. | max. | † |
| DC Characteristics for PNP Type | • | | | | |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | 50 | - | - | V |
| $I_{\rm C} = 100 \ \mu \text{A}, I_{\rm B} = 0$ | | | | | |
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | 50 | - | - | |
| $I_{\rm C} = 10 \ \mu \text{A}, \ I_{\rm E} = 0$ | , , | | | | |
| Collector cutoff current | I _{CBO} | 1 | - | 100 | nA |
| $V_{\text{CB}} = 40 \text{ V}, I_{\text{E}} = 0$ | | | | | |
| Emitter cutoff current | I _{EBO} | - | - | 164 | μΑ |
| $V_{\rm EB} = 5 \text{ V}, I_{\rm C} = 0$ | | | | | |
| DC current gain 1) | h _{FE} | 70 | _ | - | - |
| $I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 5 V | | | | | |
| Collector-emitter saturation voltage 1) | V _{CEsat} | - | _ | 0.3 | V |
| $I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 0.5 mA | | | | | |
| Input off voltage | $V_{i(off)}$ | 0.4 | - | 0.8 | |
| $I_{\rm C}$ = 100 μ A, $V_{\rm CE}$ = 5 V | | | | | |
| Input on voltage | $V_{i(on)}$ | 0.5 | - | 1.1 | |
| $I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 0.3 V | | | | | |
| Input resistor | R ₁ | 1.5 | 2.2 | 2.9 | kΩ |
| Resistor ratio | R_1/R_2 | 0.042 | 0.047 | 0.052 | - |
| AC Characteristics for PNP Type | | | | | |
| Transition frequency | f_{T} | - | 200 | - | MHz |
| $I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 5 V, f = 100 MHz | | | | | |
| Collector-base capacitance | C _{cb} | - | 3 | - | pF |
| $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$ | | | | | |

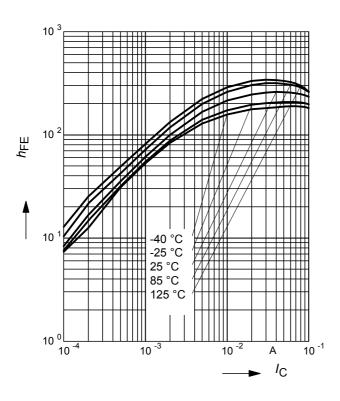
¹⁾ Pulse test: $t < 300 \mu s$; D < 2%



NPN Type

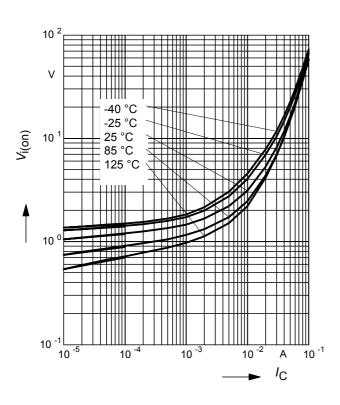
DC Current Gain $h_{FE} = f(I_C)$

 V_{CF} = 5V (common emitter configuration)



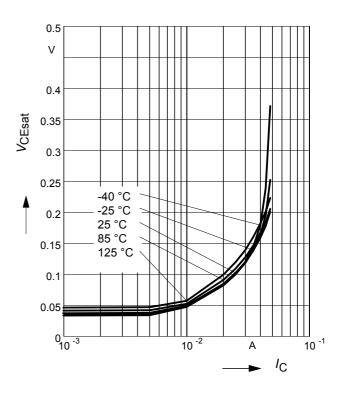
Input on Voltage $V_{i(On)} = f(I_C)$

 V_{CE} = 0.3V (common emitter configuration)



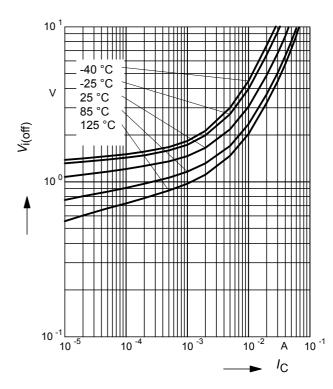
Collector-Emitter Saturation Voltage

 $V_{\text{CEsat}} = f(I_{\text{C}}), h_{\text{FE}} = 20$



Input off voltage $V_{i(Off)} = f(I_C)$

 V_{CE} = 5V (common emitter configuration)

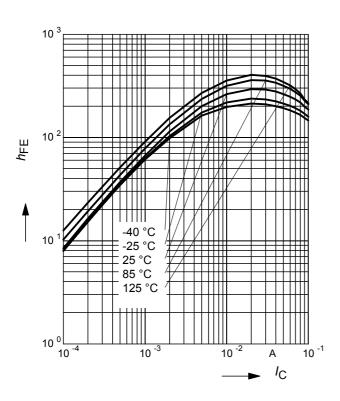




PNP Type

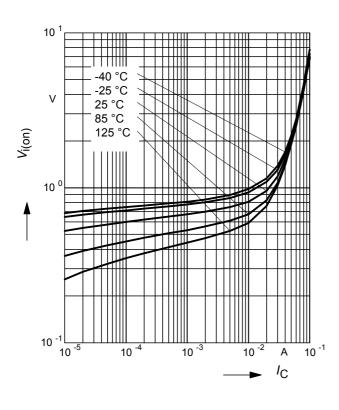
DC Current Gain $h_{FE} = f(I_C)$

 V_{CE} = 5V (common emitter configuration)



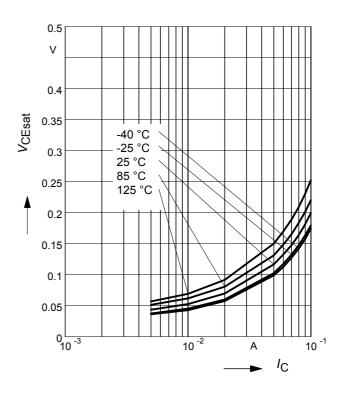
Input on Voltage $V_{i(On)} = f(I_C)$

 V_{CE} = 0.3V (common emitter configuration)



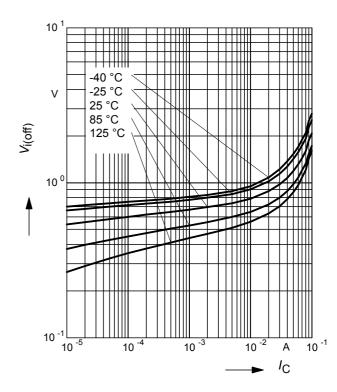
Collector-Emitter Saturation Voltage

 $V_{\text{CEsat}} = f(I_{\text{C}}), h_{\text{FE}} = 20$



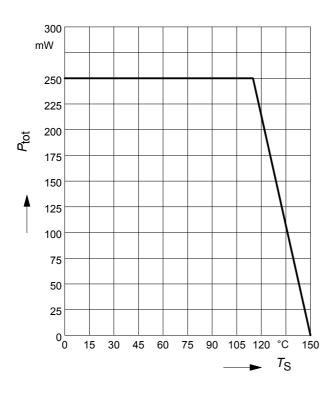
Input off voltage $V_{i(off)} = f(I_C)$

 V_{CE} = 5V (common emitter configuration)





Total power dissipation $P_{tot} = f(T_S)$

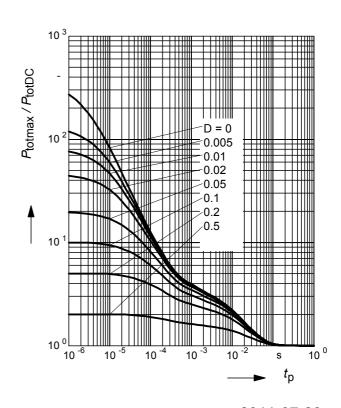


Permissible Pulse Load $R_{thJS} = f(t_p)$

10 ³

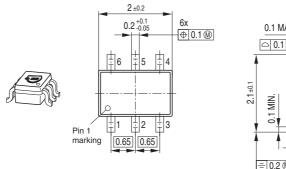
Permissible Pulse Load

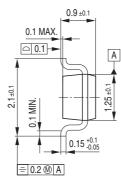
$$P_{\text{totmax}} / P_{\text{totDC}} = f(t_{p})$$



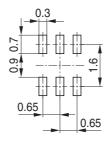


Package Outline



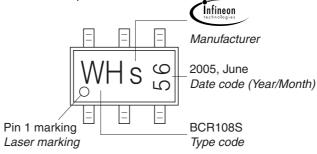


Foot Print



Marking Layout (Example)

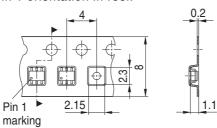
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.





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